Discrete POWER & Signal **Technologies**

TIS97

TIS97

FAIRCHILD

SEMICONDUCTOR TM



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

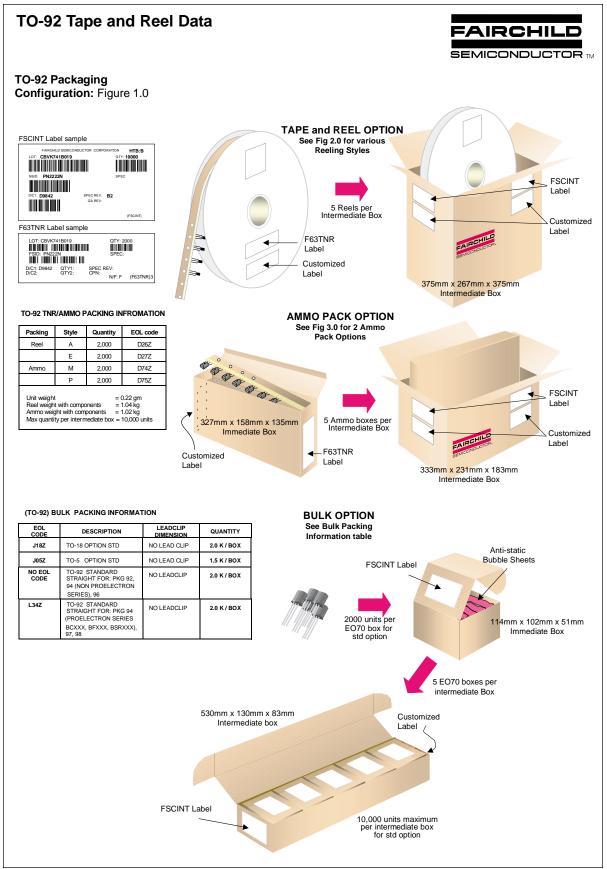
Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Мах	Units	
		TIS97		
P _D	Total Device Dissipation	625	mW	
	Derate above 25°C	5.0	mW/°C	
$R_{\theta_{JC}}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	200	°C/W	

NPN General Purpose Amplifier (continued)

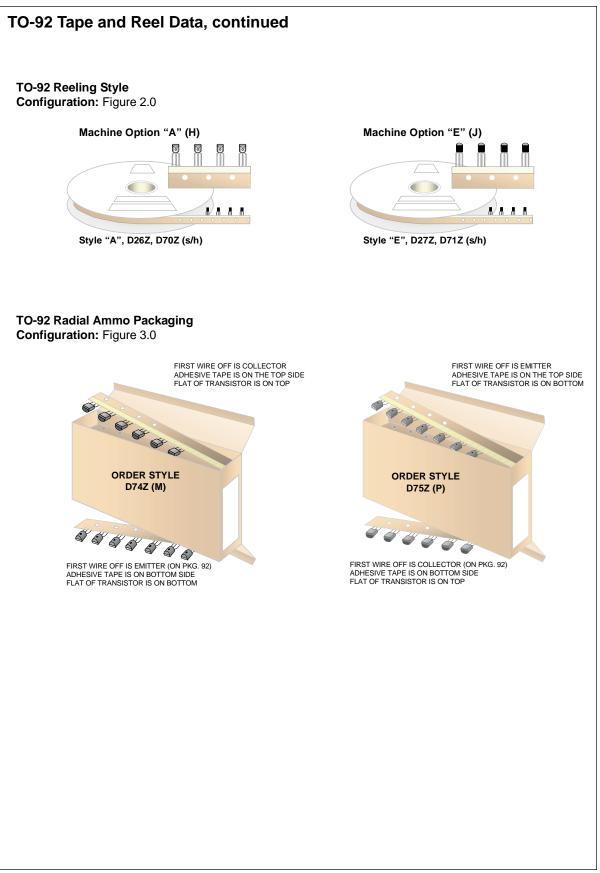
TIS97

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 40 \text{ V}, I_E = 0$ $V_{CB} = 60 \text{ V}, I_E = 0$		10 10	nA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 6.0 \text{ V}, I_{C} = 0$		20	nA
	DC Current Gain Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{V}, I_{C} = 100 \mu\text{A}$	250 0.45	700 0.65	V
SMALL S	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	0.45	0.65	
SMALL S C _{cb}	Base-Emitter On Voltage IGNAL CHARACTERISTICS Collector-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CB} = 5.0 V, f = 1.0 M\text{Hz}$		0.65 4.0	pF
SMALL S C _{cb} C _{eb}	Base-Emitter On Voltage IGNAL CHARACTERISTICS Collector-Base Capacitance Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CB} = 5.0 V, f = 1.0 M\text{Hz}$ $V_{EB} = 0.5 V, f = 1.0 M\text{Hz}$	0.45	0.65	
SMALL S C _{cb} C _{eb}	Base-Emitter On Voltage IGNAL CHARACTERISTICS Collector-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CB} = 5.0 \text{V}, f = 1.0 \text{MHz}$ $V_{EB} = 0.5 \text{V}, f = 1.0 \text{MHz}$ $I_C = 100 \mu\text{A}, V_{CE} = 5.0 \text{V}, f = 1.0 \text{kHz}$	0.45	0.65 4.0	pF
SMALL S C _{cb} C _{eb} h _{fe}	Base-Emitter On Voltage IGNAL CHARACTERISTICS Collector-Base Capacitance Emitter-Base Capacitance Small-Signal Current Gain	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CB} = 5.0 V, f = 1.0 M\text{Hz}$ $V_{EB} = 0.5 V, f = 1.0 M\text{Hz}$ $I_C = 100 \mu\text{A}, V_{CE} = 5.0 V,$	0.45	0.65 4.0 16	pF
h _{FE} V _{BE(on)} SMALL S C _{cb} C _{eb} h _{fe} NF	Base-Emitter On Voltage IGNAL CHARACTERISTICS Collector-Base Capacitance Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CB} = 5.0 \text{V}, f = 1.0 \text{MHz}$ $V_{EB} = 0.5 \text{V}, f = 1.0 \text{MHz}$ $I_C = 100 \mu\text{A}, V_{CE} = 5.0 \text{V}, f = 1.0 \text{kHz}$ $I_C = 10 \text{mA}, V_{CE} = 5.0 \text{V},$	0.45 1.0 250	0.65 4.0 16	pF



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Definition of Terms

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